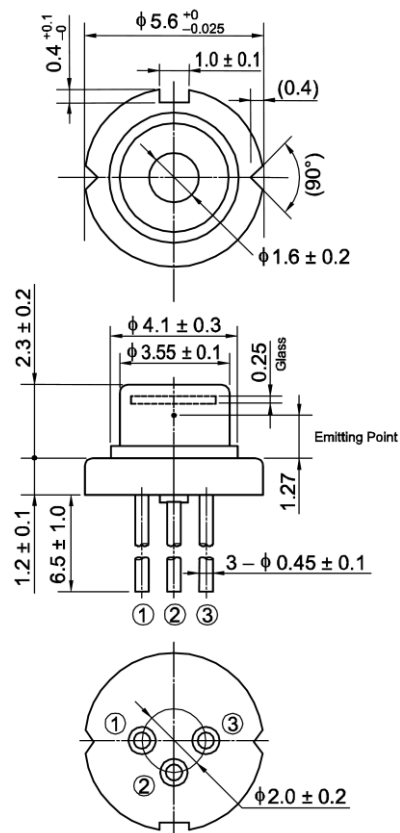


HL65261MG/262MG/263MG/264MG

658nm/85mW (CW)/310mW (Pulse)

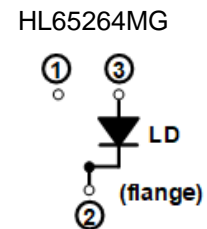
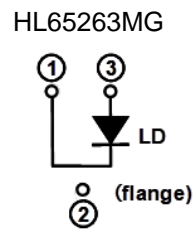
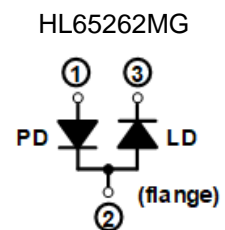
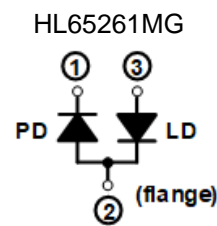
AlGaInP Laser Diode

Outline



(Unit: mm)

Internal Circuit



Features

- Visible light output: 658nm Typ.
- Optical output power: 85mW (CW), 310mW (Pulse)
- Low operating current:
 - 90mA Typ. (80mW (CW))
 - 245mA Typ. (300mW (Pulse))
- Operating temperature: +60°C (CW), +75°C (Pulse)
- Single transverse mode
- TE mode oscillation

Application

- Sensor application
- Light source of optical equipment

HL65261MG/262MG/263MG/264MG

Data Sheet

Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Ratings	Unit
Optical output power	Po	85	mW
Pulse optical output power ^{Note1)}	Po(Pulse)	310	mW
LD reverse voltage	V _{R(LD)}	2	V
PD reverse voltage ^{Note2)}	V _{R(PD)}	30	V
Operating temperature	Topr(CW)	-10 ~ +60	°C
Pulse Operating temperature ^{Note1)}	Topr(Pulse)	-10 ~ +75	°C
Storage temperature	Tstg	-40 ~ +85	°C

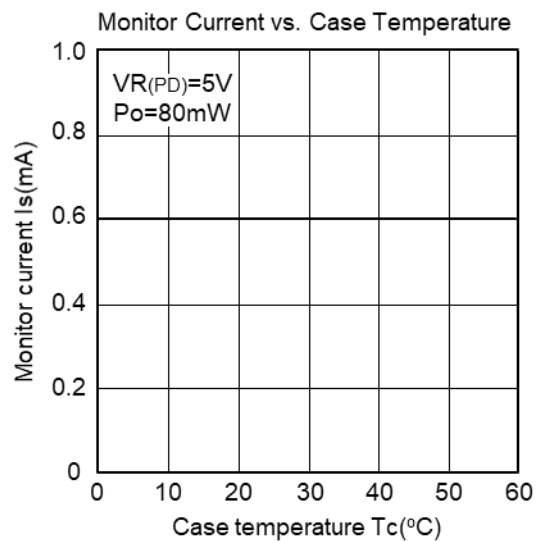
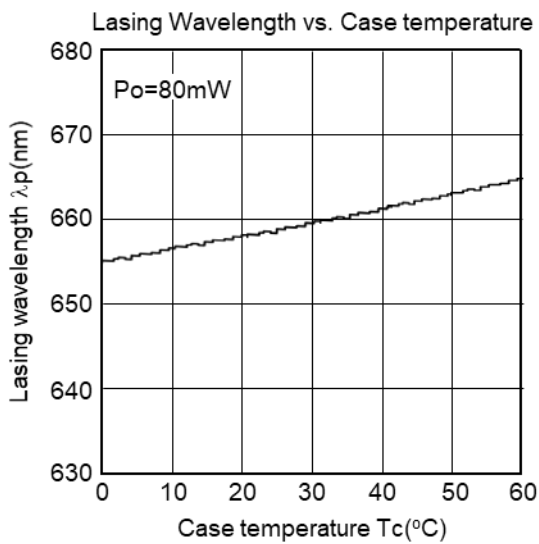
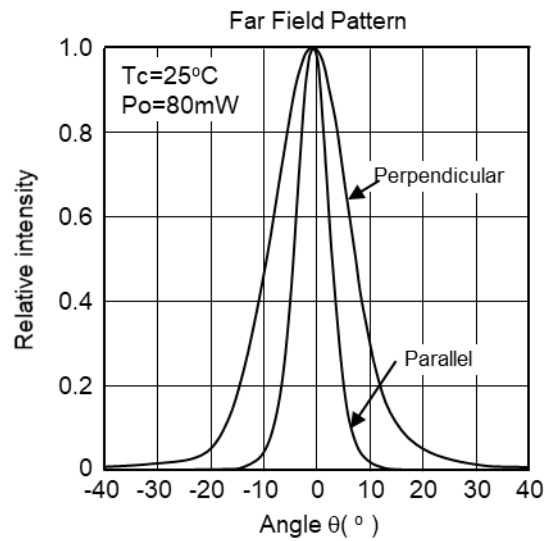
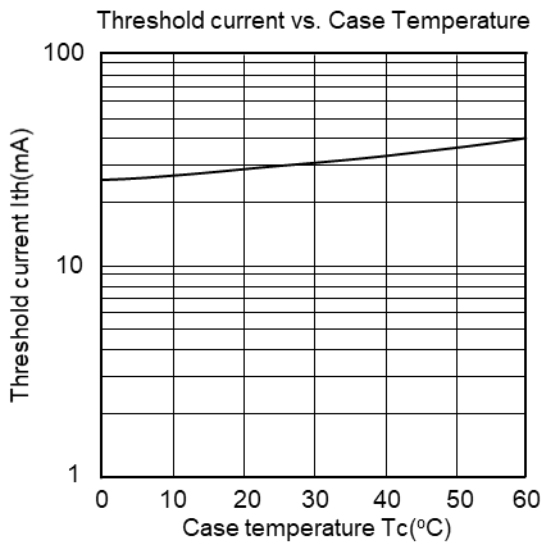
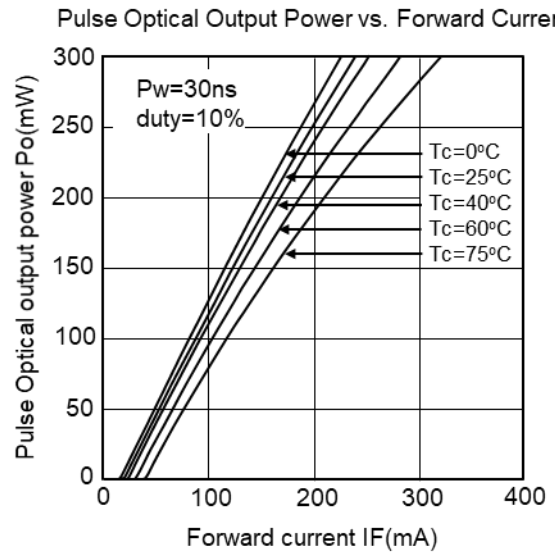
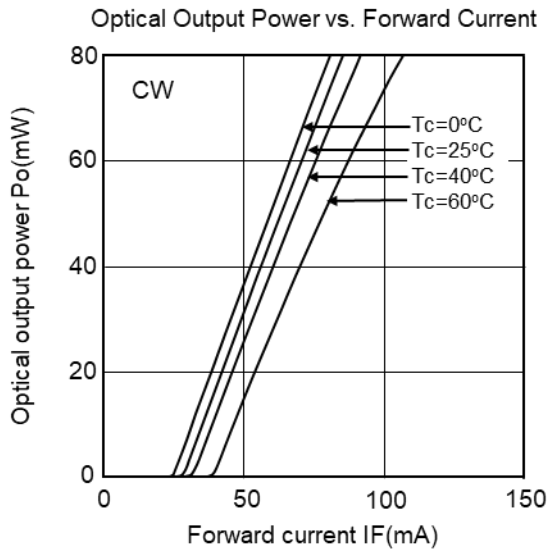
Optical and Electrical Characteristics (Tc=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Threshold current	I _{th}	-	30	50	mA	-
Operating current	I _{op}	-	90	120	mA	Po=80mW
	I _{op} (Pulse)	-	245	-	mA	Po(Pulse)=300mW Note 1
Operating voltage	V _{op}	-	2.6	3.3	V	Po=80mW
Beam divergence Parallel to the junction	θ _{//}	4	7.5	11	°	Po=80mW, FWHM
Beam divergence Perpendicular to the junction	θ _⊥	11	15	19	°	Po=80mW, FWHM
Lasing wavelength	λ _p	652	658	665	nm	Po=80mW
Monitor current ^{Note2)}	I _s	0.1	0.6	1.5	mA	Po=80mW V _{R(PD)} =5V

Note1) Pulse condition: Pulse width = 10nsec, duty = 10%

Note2) Not applicable to HL65263MG,HL65264MG.

Typical Characteristic Curves



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